

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

2SK2987

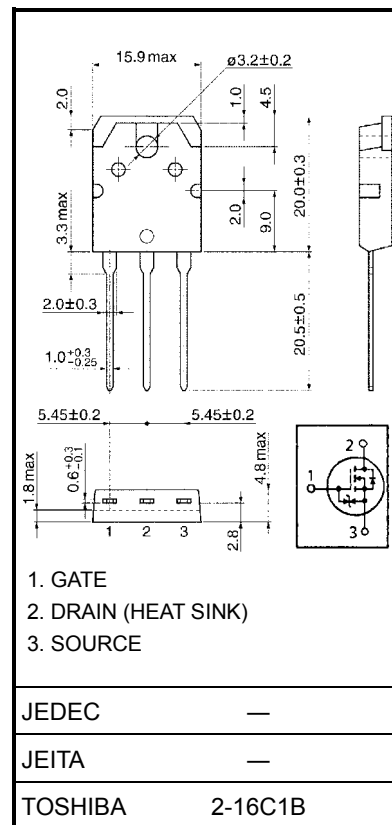
DC-DC Converter, Relay Drive and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance : $R_{DS(ON)} = 4.5 \text{ m}\Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 80 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 100 \text{ }\mu\text{A}$ (max) ($V_{DS} = 60 \text{ V}$)
- Enhancement-mode : $V_{th} = 1.3 \sim 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	60	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	60	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	70	A
	Pulse (Note 1)	I_{DP}	280	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	150	W
Single pulse avalanche energy (Note 2)		E_{AS}	490	mJ
Avalanche current		I_{AR}	70	A
Repetitive avalanche energy (Note 3)		E_{AR}	15	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight: 4.6 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ\text{C} / \text{W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

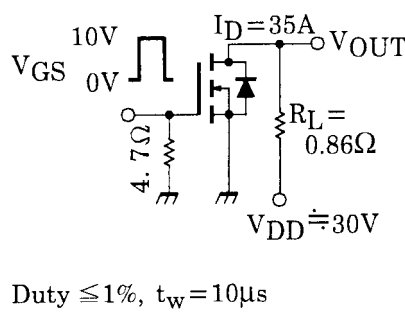
Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 136 \text{ }\mu\text{H}$, $I_{AR} = 70 \text{ A}$, $R_G = 25 \text{ }\Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

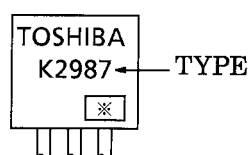
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain cut-off current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	60	—	—	V
		V _{(BR) DSX}	I _D = 10 mA, V _{GS} = -20 V	40	—	—	
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	—	2.5	V
Drain-source ON resistance		R _{DS (ON)}	V _{GS} = 10 V, I _D = 35 A	—	4.5	5.8	mΩ
			V _{GS} = 4 V, I _D = 35 A	—	5.8	10	
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 35 A	40	80	—	S
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	9300	—	pF
Reverse transfer capacitance		C _{rss}		—	910	—	
Output capacitance		C _{oss}		—	1435	—	
Switching time	Rise time	t _r		—	18	—	ns
	Turn-on time	t _{on}		—	50	—	
	Fall time	t _f		—	110	—	
	Turn-off time	t _{off}		—	480	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ 48 V, V _{GS} = 10 V, I _D = 70 A	—	210	—	nC
Gate-source charge		Q _{gs}		—	145	—	
Gate-drain (“miller”) Charge		Q _{gd}		—	65	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	70	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	280	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 70 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 70 \text{ A}, V_{GS} = 0 \text{ V}, dI_{DR}/dt = 50 \text{ A}/\mu\text{s}$	—	60	—	ns
Reverse recovery charge	Q_{rr}		—	50	—	nC

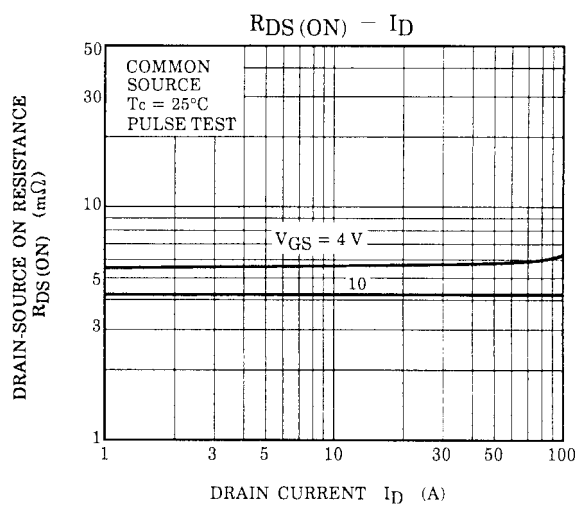
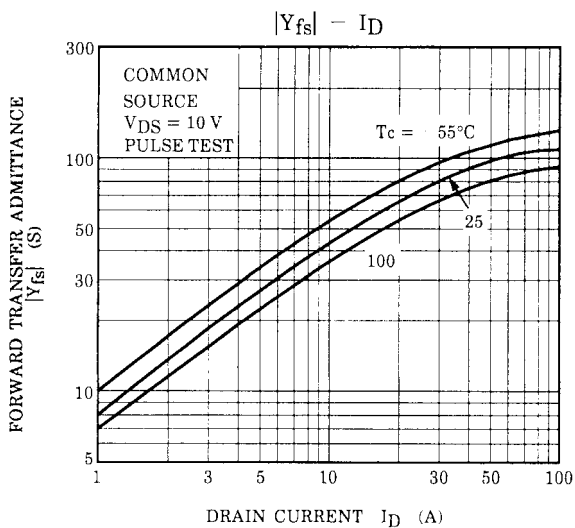
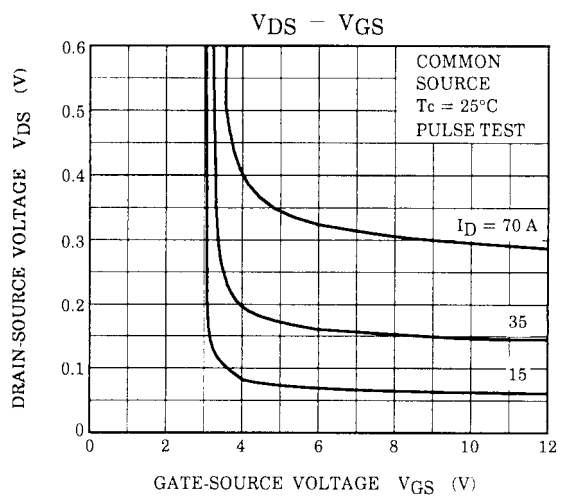
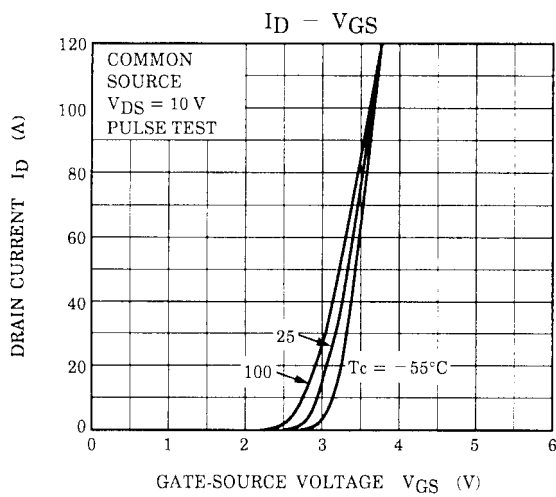
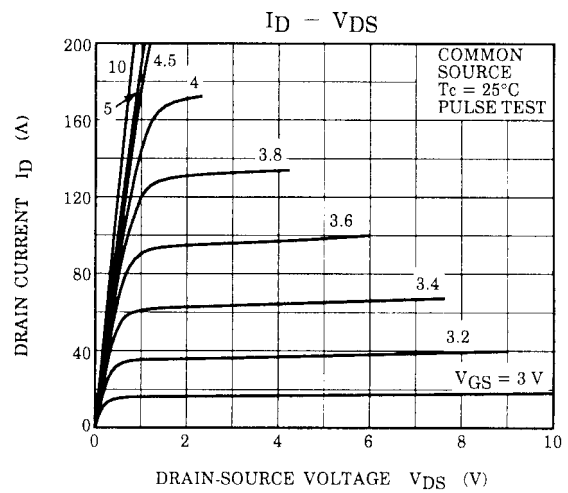
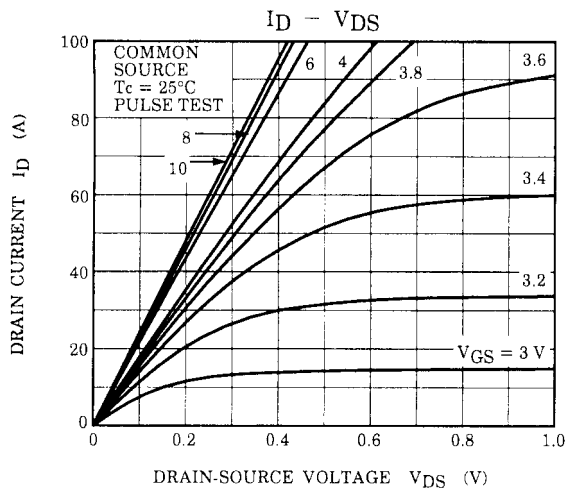
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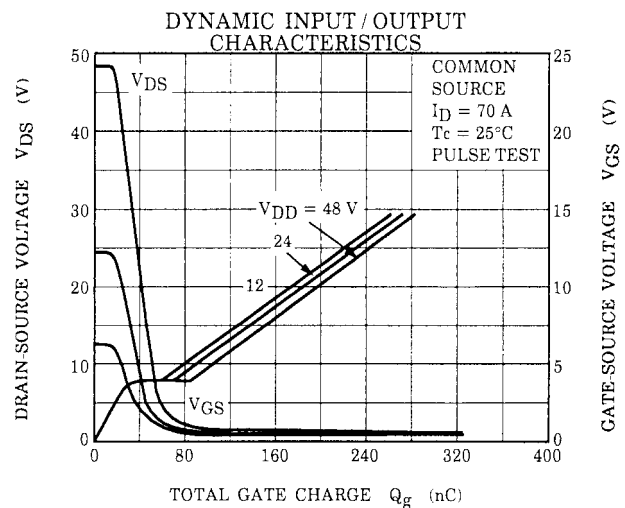
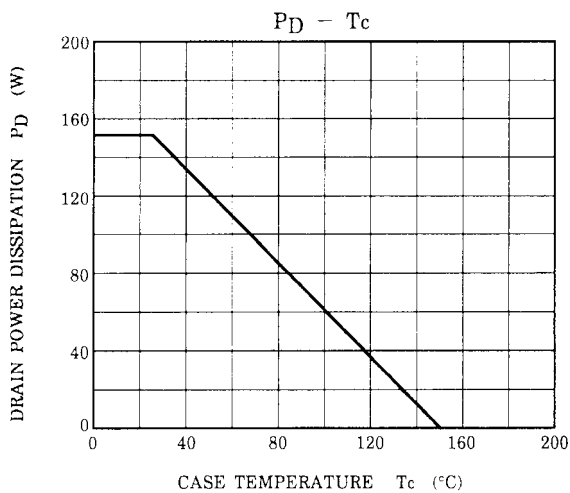
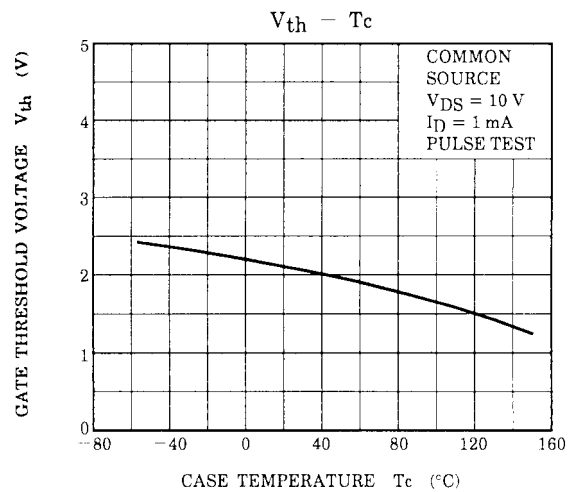
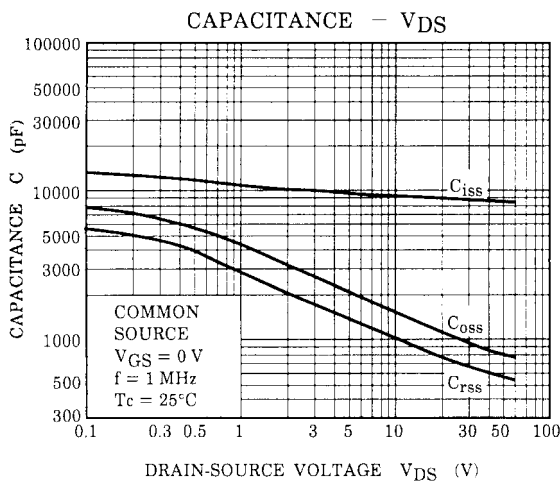
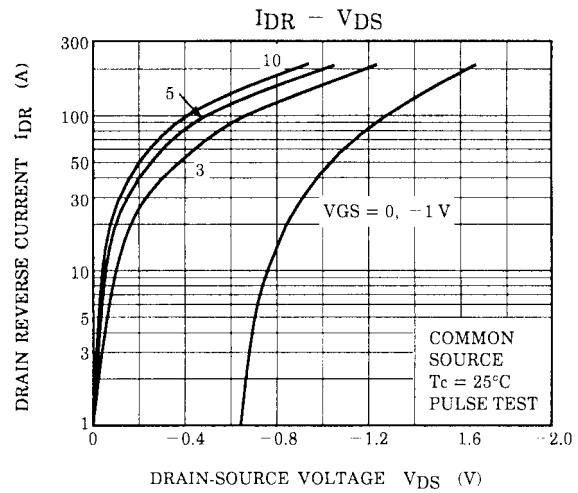
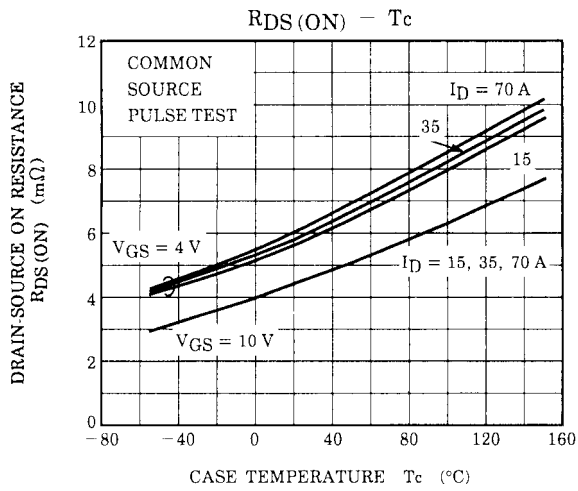


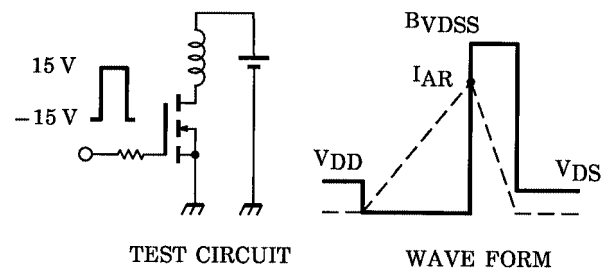
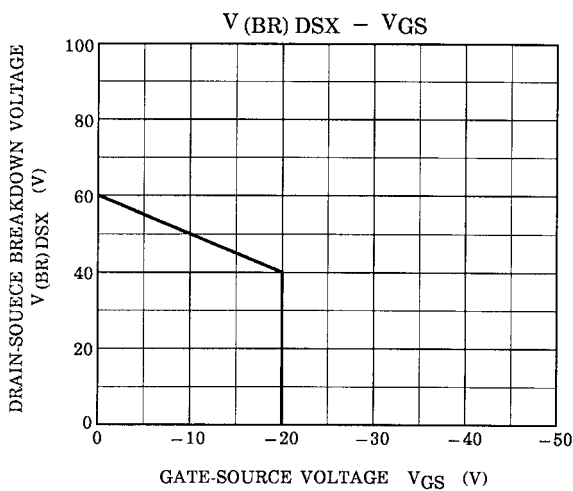
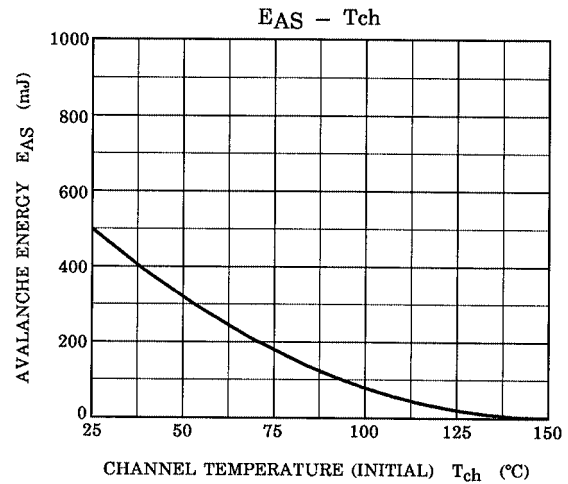
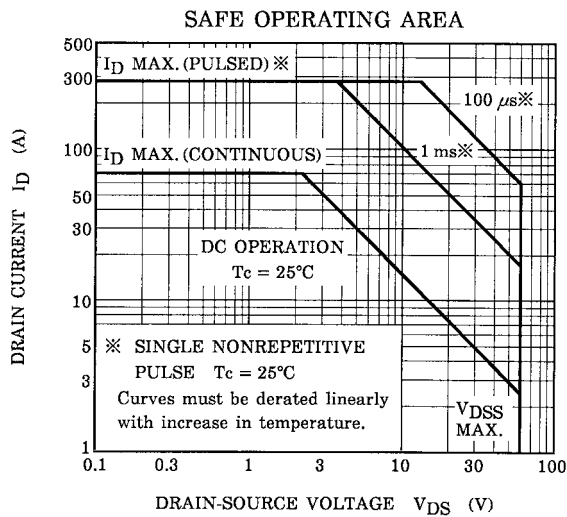
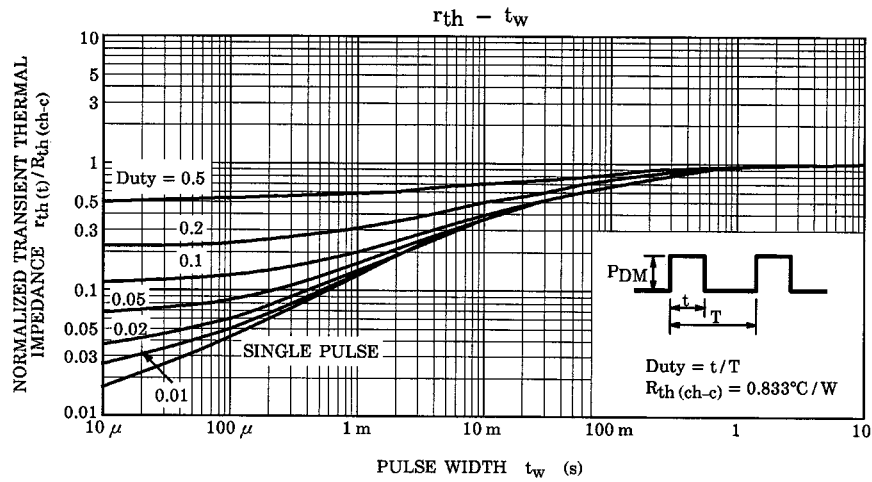
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







$$R_G = 25 \, \Omega$$

$$V_{DD} = 25 \, \text{V}, L = 136 \, \mu\text{H}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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